FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty Docket	U.S. Application No.: To be assigned		
				02DCOAI010-CA			
			Applicant Naokatusu IKEGAMI				
				U.S. Filing Date: July 24, 2003	Group To be assigned		
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE				-		
	AF		_				
	AG	·					
	AH						
	Al ·	·					
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
		Document Number	Pub. Date	. Country	Class	Sub- Class	Translation
	AL						
	AM						
	AN						
	AO						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
A	AR	"Deep Sub-0.1µm MOSFET's with very thin SOI layer for ultra-low power consumption", C-II vol. J81-C-II No. 3, pp 313-319 published in March, 1998 by The Institute of Electronics, Information and Communication Engineers Author: Makoto TAKAMIYA, Yuri YASUDA and Toshiro HIRAMOTO Note: English Summary is attached					
H	AS .	"Optimization of Series Resistance in Sub-0.2 mm SOI MOSFET's", IEEE Electron device letters, Vol. 15, No. 09 Page 363 published in September,1994 Author: Lisa T. Su, Melanie J. Sherony, Hang Hu, James E. Chung and Dimitri A. Antonidis					
Examiner // Profile					Date Considered 12/28/05		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							